

# JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

# **SOD-123 Plastic-Encapsulate Diode**

## B5817W-5819W SCHOTTKY BARRIER DIODE

#### **FEATURES**

For use in low voltage, high frequency inverters Free wheeling, and polarity protection applications.

MARKING: B5817W: SJ

B5818W:SK B5819W: SL



## Maximum Ratings and Electrical Characteristics, Single Diode @T<sub>A</sub>=25℃

| Parameter   | Symbol   | B5817W | B5818W               | B5819W | Unit |
|---|--|--------|----------------------|--------|------|
| Non-Repetitive Peak reverse voltage   | $V_{RM}$   | 20     | 30                   | 40     | V    |
| Peak repetitive Peak reverse voltage<br>Working Peak Reverse Voltage<br>DC Blocking Voltage | V <sub>RRM</sub><br>V <sub>RWM</sub><br>V <sub>R</sub> | 20     | 30                   | 40     | V    |
| RMS Reverse Voltage   | $V_{R(RMS)}$   | 14     | 21                   | 28     | V    |
| Average Rectified Output Current  | Io   |        | Α                    |        |      |
| Peak forward surge current @=8.3ms  | I <sub>FSM</sub>                                       |        | Α                    |        |      |
| Repetitive Peak Forward Current   | $I_{FRM}$  |        | mA                   |        |      |
| Power Dissipation   | Pd   |        | mW                   |        |      |
| Thermal Resistance Junction to Ambient  | $R_{\theta JA}$  |        | K/W                  |        |      |
| Storage temperature   | T <sub>STG</sub>                                       |        | $^{\circ}\mathbb{C}$ |        |      |

## ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

| Parameter                       | Symbol            | Test c  | onditions                                | MIN            | MAX           | UNIT |
|---------------------------------|-------------------|---|--|----------------|---------------|------|
| Reverse breakdown voltage       | V <sub>(BR)</sub> | I <sub>R</sub> = 1mA  | B5817W<br>B5818W<br>B5819W               | 20<br>30<br>40 |               | V    |
| Reverse voltage leakage current | I <sub>R</sub>    | V <sub>R</sub> =20V<br>V <sub>R</sub> =30V<br>V <sub>R</sub> =40V | B5817W<br>B5818W<br>B5819W               |                | 1             | mA   |
| Forward voltage                 | V <sub>F</sub>    | B5817W  | I <sub>F</sub> =1A<br>I <sub>F</sub> =3A |                | 0.45<br>0.75  | V    |
|                                 |                   | B5818W  | I <sub>F</sub> =1A<br>I <sub>F</sub> =3A |                | 0.55<br>0.875 | ٧    |
|                                 |                   | B5819W  | I <sub>F</sub> =1A<br>I <sub>F</sub> =3A |                | 0.6<br>0.9    | V    |
| Diode capacitance               | C <sub>D</sub>    | V <sub>R</sub> =4V, f=1MHz  |  |                | 120           | pF   |

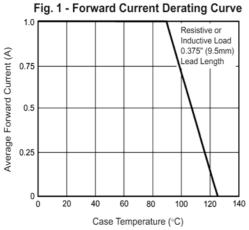


Fig. 2 - Maximum Non-Repetitive Peak **Forward Surge Current** Peak Forward Surge Current (A) 20 15 10 0 100 10 Number of Cycles at 60 Hz

